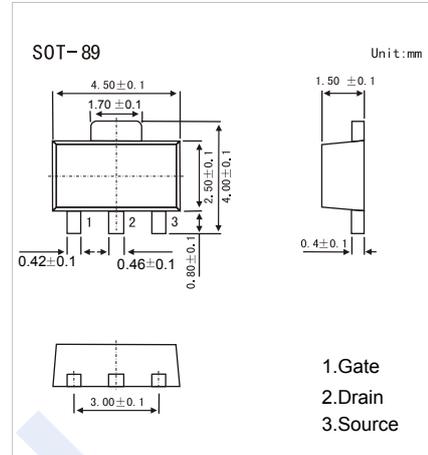
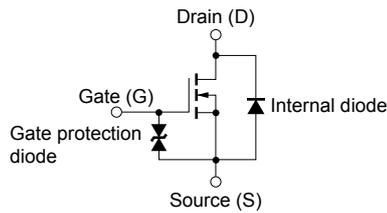


## N-Channel MOSFET

### 2SK2109

#### Features

- $V_{DS} (V) = 60V$
- $I_D = 0.5A$
- $R_{DS(ON)} < 1 \Omega$  ( $V_{GS} = 4V$ )
- $R_{DS(ON)} < 0.8 \Omega$  ( $V_{GS} = 10V$ )



#### Absolute Maximum Ratings $T_a = 25^\circ C$

Parameter	Symbol	Rating	Unit
Drain-Source Voltage	$V_{DS}$	60	V
Gate-Source Voltage	$V_{GS}$	$\pm 20$	
Continuous Drain Current	$I_D$	0.5	A
Pulsed Drain Current (Note.1)	$I_{DM}$	1	
Power Dissipation	$P_D$	2	W
Junction Temperature	$T_J$	150	$^\circ C$
Storage Temperature Range	$T_{stg}$	-55 to 150	

Note.1:  $PW \leq 10ms$ , Duty Cycle  $\leq 50\%$

#### Electrical Characteristics $T_a = 25^\circ C$

Parameter	Symbol	Test Conditions	Min	Typ	Max	Unit
Drain-Source Breakdown Voltage	$V_{DSS}$	$I_D = 250 \mu A$ , $V_{GS} = 0V$	60			V
Zero Gate Voltage Drain Current	$I_{DSS}$	$V_{DS} = 60V$ , $V_{GS} = 0V$			1	$\mu A$
Gate-Body Leakage Current	$I_{GSS}$	$V_{DS} = 0V$ , $V_{GS} = \pm 20V$			$\pm 10$	$\mu A$
Gate Cut-off Voltage	$V_{GS(off)}$	$V_{DS} = 10V$ , $I_D = 1mA$	0.8		2	V
Static Drain-Source On-Resistance	$R_{DS(on)}$	$V_{GS} = 4V$ , $I_D = 0.3A$			1	$\Omega$
		$V_{GS} = 10V$ , $I_D = 0.3A$			0.8	
Forward Transconductance	$g_{FS}$	$V_{DS} = 10V$ , $I_D = 0.3A$	0.4			S
Input Capacitance	$C_{iss}$	$V_{GS} = 0V$ , $V_{DS} = 10V$ , $f = 1MHz$		111		$\mu F$
Output Capacitance	$C_{oss}$			55		
Reverse Transfer Capacitance	$C_{rss}$			19		
Turn-On DelayTime	$t_{d(on)}$	$V_{GS(on)} = 10V$ , $V_{DS} = 25V$ , $I_D = 0.3A$ , $R_L = 83 \Omega$ , $R_G = 10 \Omega$		2.2		ns
Turn-On Rise Time	$t_r$			1.5		
Turn-Off DelayTime	$t_{d(off)}$			35		
Turn-Off Fall Time	$t_f$			19		

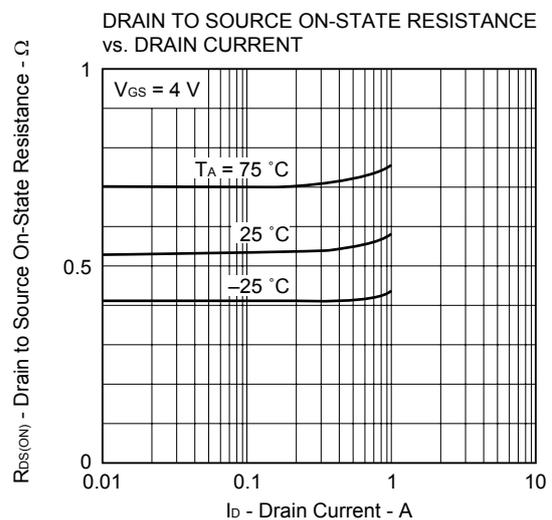
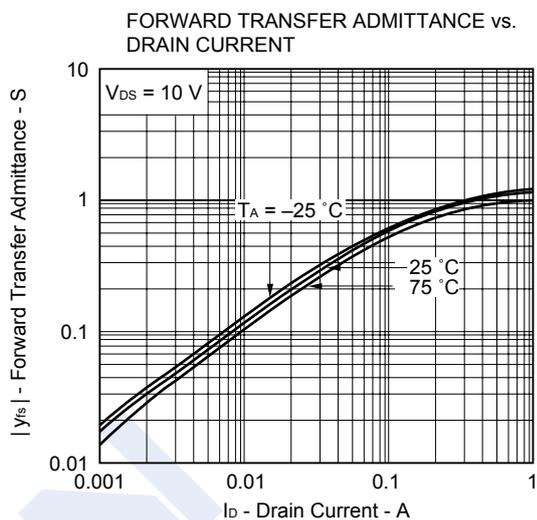
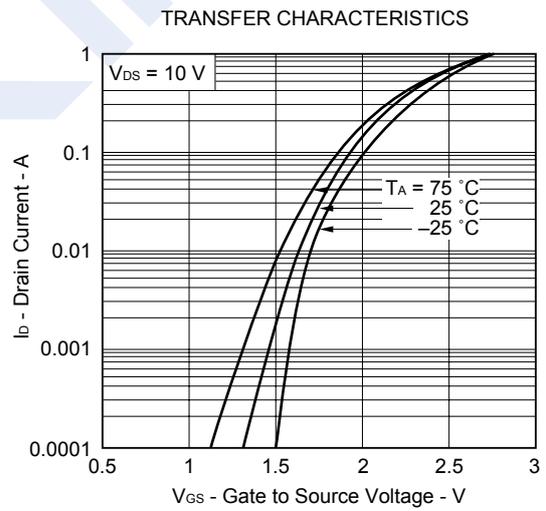
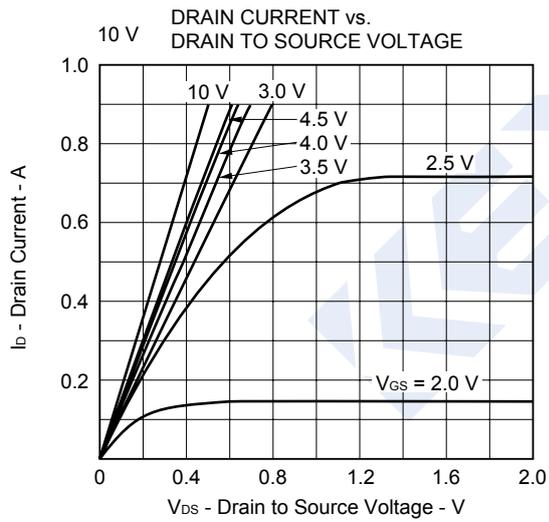
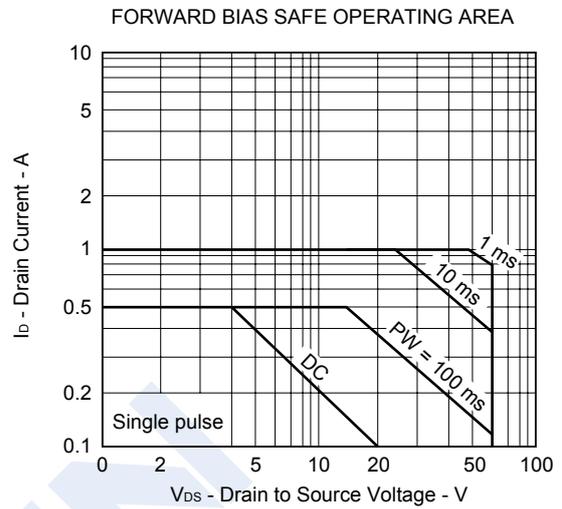
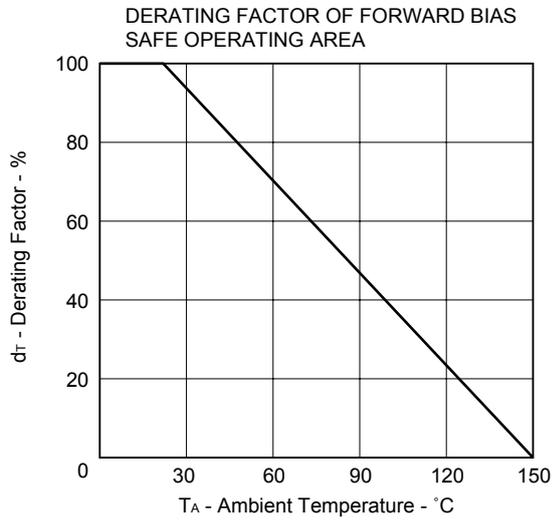
#### Marking

Marking	NS
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# N-Channel MOSFET

## 2SK2109

■ Typical Characteristics



## N-Channel MOSFET 2SK2109

### Typical Characteristics

